

isc Silicon PNP Power Transistor

2SA1718

DESCRIPTION

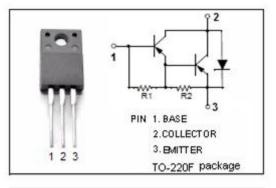
- Low Collector Saturation Voltage :V_{CE(sat)}= -0.5(V)(Max)@I_C= -2A
- High Switching Speed
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

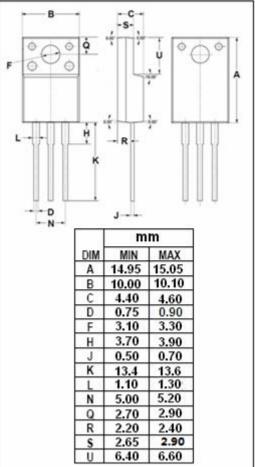
APPLICATIONS

· Designed for audio and general purpose applications.



ABSOLUTE MAXIMUM RATINGS(Ta=25℃)





1



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA ; I _B = 0	-100			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -2mA			-1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -2A; I _B = -2mA			-2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -100V; I _E = 0			-10	μ Α
I _{EBO}	Emitter Cutoff Current	V _{EB} = -7V; I _C = 0			-5	mA
h _{FE-1}	DC Current Gain	I _C = -2A ; V _{CE} = -2V	2K		20K	
h _{FE-2}	DC Current Gain	I _C = -4A ; V _{CE} = -2V	500			

• h_{FE-1} Classifications

М	L	к
2K-5K	4K-10K	8K-20K

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